

ABSTRACT OF THE DISCLOSURE

Semiconductor light emitting devices and methods of producing same are provided. The semiconductor light emitting devices include a substrate that has a surface including a difference-in-height portion composed of, for example, a wurtzite compound. A crystal growth layer is formed in the substrate surface wherein at least a portion of which is oriented along an inclined plane with respect to a principal plane of the substrate. The semiconductor device includes a first conductive layer, an active layer and a second conductive layer formed on the crystal layer in a stacked arrangement and oriented along the inclined place.